UHF power LDMOS transistor Rev. 2 — 30 August 2016

#### **Product profile** 1.

## 1.1 General description

A 750 W LDMOS RF power transistor for asymmetrical broadcast Doherty transmitter applications which operates at 150 W DVB-T average power. The excellent ruggedness of this device makes it ideal for digital and analog transmitter applications.

#### **Application information** Table 1.

RF performance at  $V_{DS}$  = 50 V in an asymmetrical Doherty application.

Test signal	f	P <sub>L(AV)</sub>	G <sub>p</sub>	η <sub>D</sub>	IMD <sub>shldr</sub>	PAR
	(MHz)	(W)	(dB)	(%)	(dBc)	(dB)
DVB-T (8k OFDM)	470 to 608	150	17	52	-38	8 <u>[1]</u>
	600 to 700	150	17	50	-38	8 <u>[1]</u>
	650 to 790	150	15	49	-38	8 <u>[1]</u>

[1] PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

## 1.2 Features and benefits

- Designed for asymmetric Doherty operation
- Very high efficiency enabling air cooled high power transmitters
- Integrated ESD protection
- Excellent ruggedness
- High power gain
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

## 1.3 Applications

- Broadcast transmitter applications in the UHF band
- Digital broadcasting

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# 2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
BLF888E	(SOT539A)		
1	drain1 (peak)		
2	drain2 (main)		
3	gate1 (peak)		
4	gate2 (main)	3 4	3 5
5	source	[1]	
			۲۳ ا
			2 sym117
BLF888E	S (SOT539B)		
1	drain1 (peak)		
2	drain2 (main)		
3	gate1 (peak)	5	
4	gate2 (main)		3 5
5	source	[1]	
			l IF-1
			2 sym117

[1] Connected to flange.

# 3. Ordering information

### Table 3.Ordering information

Type number	Packag	Package				
	Name	Description	Version			
BLF888E	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A			
BLF888ES	-	earless flanged balanced ceramic package; 4 leads	SOT539B			

# 4. Limiting values

### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS(amp)main</sub>	main amplifier drain-source voltage		-	104	V
V <sub>DS(amp)peak</sub>	peak amplifier drain-source voltage		-	120	V
V <sub>GS(amp)main</sub>	main amplifier gate-source voltage		-0.5	+11	V
V <sub>GS(amp)peak</sub>	peak amplifier gate-source voltage		-6	+11	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

Product data sheet

# 5. Thermal characteristics

Table 5.	Thermal	characteristics
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Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case} = 90 \ ^{\circ}C; \ V_{DS} = 50 \ V; $ [1] $I_{DS} = 3 \ A \ (main); \ I_{DS} = 0 \ A \ (peak)$	0.29	K/W
		$T_{case} = 90 \ ^{\circ}C; V_{DS} = 50 \ V;$ $P_{L} = 150 \ W; PAR = 8 \ dB$	0.19	K/W

[1] Measured under DC test conditions, with peak section off.

[2] Measured in an ultra-wide Doherty application, using DVB-T (8k OFDM) signal, PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

# 6. Characteristics

### Table 6. DC characteristics

 $T_i$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Main dev	rice	1				-
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 2.4 mA	104	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 240 mA	1.25	1.75	2.25	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V	-	-	2.8	μA
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	38	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V	-	-	280	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ I <sub>D</sub> = 8.5 A	-	120	-	mΩ
Peak dev	vice	1				
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	V <sub>GS</sub> = 0 V; I <sub>D</sub> = 3.6 mA	125	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 360 mA	1.33	1.83	2.33	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V	-	-	2.8	μA
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	57	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V	-	-	280	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ I <sub>D</sub> = 12.6 A	-	90	-	mΩ

### Table 7.AC characteristics

 $T_j$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main device						
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	210	-	pF
C <sub>oss</sub>	output capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	67	-	pF
C <sub>rss</sub>	reverse transfer capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	1.35	-	pF

### Table 7. AC characteristics ...continued

 $T_i$  = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Peak device						
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	315	-	pF
C <sub>oss</sub>	output capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	105	-	pF
C <sub>rss</sub>	reverse transfer capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	1.5	-	pF

### Table 8. RF characteristics

RF characteristics in Ampleon production test circuit,  $T_{case} = 25 \, ^{\circ}C$ ; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
DVB-T (8	DVB-T (8k OFDM), Doherty operation							
V <sub>DS</sub>	drain-source voltage		-	50	-	V		
I <sub>Dq</sub>	quiescent drain current	peak section: $V_{GS}$ = 1.3 V below $V_{GS(th)}$ (peak)	-	600	-	mA		
P <sub>L(AV)</sub>	average output power	f = 550 MHz	-	150	-	W		
G <sub>p</sub>	power gain	f = 550 MHz	15.8	17	-	dB		
$\eta_D$	drain efficiency	f = 550 MHz	48	52	-	%		
PAR	peak-to-average ratio	f = 550 MHz	7.2	7.8	-	dB		

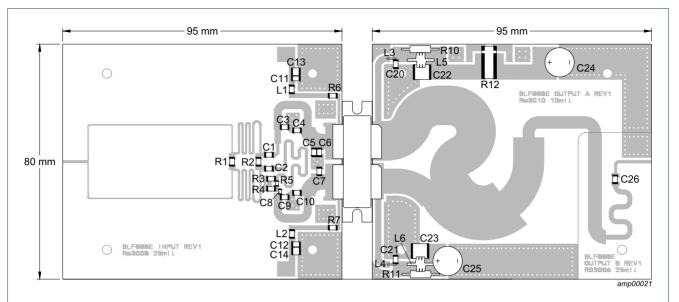
# 7. Test information

## 7.1 Ruggedness in Doherty operation

The BLF888E and BLF888ES are capable of withstanding a load mismatch corresponding to VSWR  $\ge$  40 : 1 through all phases under the following conditions: V<sub>DS</sub> = 50 V; f = 550 MHz at rated load power.

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### 7.2 Test circuit



Printed-Circuit Board (PCB): Rogers 3006;  $\varepsilon_r$  = 6.5 F/m; height = 0.635 mm; Cu (top/bottom metalization); thickness copper plating = 29.6  $\mu$ m; Rogers 3010:  $\epsilon_r$  = 10 F/m; height = 0.254 mm

See Table 9 for a list of components.

#### Component layout for production RF test circuit Fig 1.

#### Table 9. List of components

Component	Description	Value	Remarks			
C1, C2	multilayer ceramic chip capacitor	51 pF [1]	ATC 100B			
C3	multilayer ceramic chip capacitor	11 pF [1]	ATC 100B			
C4	multilayer ceramic chip capacitor	13 pF [1]	ATC 100B			
C5, C6	multilayer ceramic chip capacitor	24 pF [1]	ATC 100B			
C7	multilayer ceramic chip capacitor	33 pF [1]	ATC 100B			
C8	multilayer ceramic chip capacitor	51 pF [2]	ATC 100A			
C9	multilayer ceramic chip capacitor	12 pF [1]	ATC 100B			
C10	multilayer ceramic chip capacitor	20 pF [1]	ATC 100B			
C11, C12	multilayer ceramic chip capacitor	43 pF [1]	ATC 100B			
C13, C14	multilayer ceramic chip capacitor	4.7 μF				
C20, C21	electrolytic capacitor	100 pF [1]	ATC 100B			
C22, C23	multilayer ceramic chip capacitor	4.7 μF, 100 V				
C25, C25	electrolytic capacitor	470 μF, 63 V				
C26	multilayer ceramic chip capacitor	47 pF [1]	ATC 100B			
L1, L2	inductor	10 nH	Coilcraft			
L3, L4	inductor	0.5 turn, D = 2 mm, d = 1mm				
L5, L6	inductor	1 turn, D = 5 mm, d = 1mm				
R1	chip resistor	90 Ω				

### For test circuit see Figure 1 (

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### Table 9. List of components ...continued

r of test circuit see <u>rigure 1</u> .						
Component	Description	Value	Remarks			
R2	chip resistor	265 Ω				
R3, R4	chip resistor	360 Ω				
R5	chip resistor	15 Ω				
R6	chip resistor	75 Ω				
R7	chip resistor	5 Ω				
R10, R11	wire resistor	1 Ω				
R12	shunt resistor	0.01 Ω				

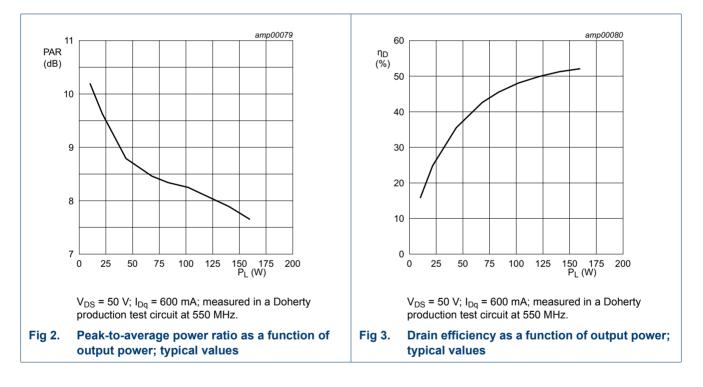
For test circuit see Figure 1.

[1] American Technical Ceramics type 100B or capacitor of same quality

[2] American Technical Ceramics type 100A or capacitor of same quality

### 7.3 Graphical data

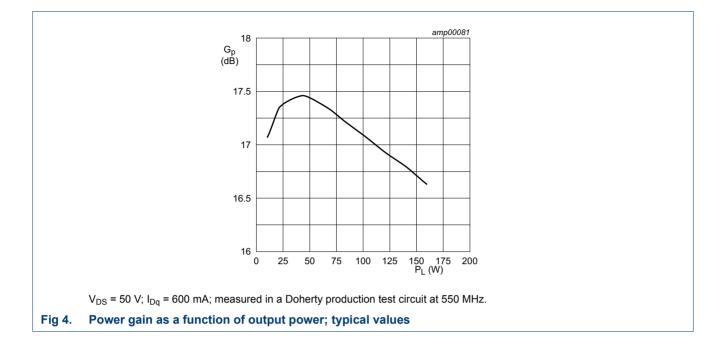
### 7.3.1 DVB-T in production test circuit



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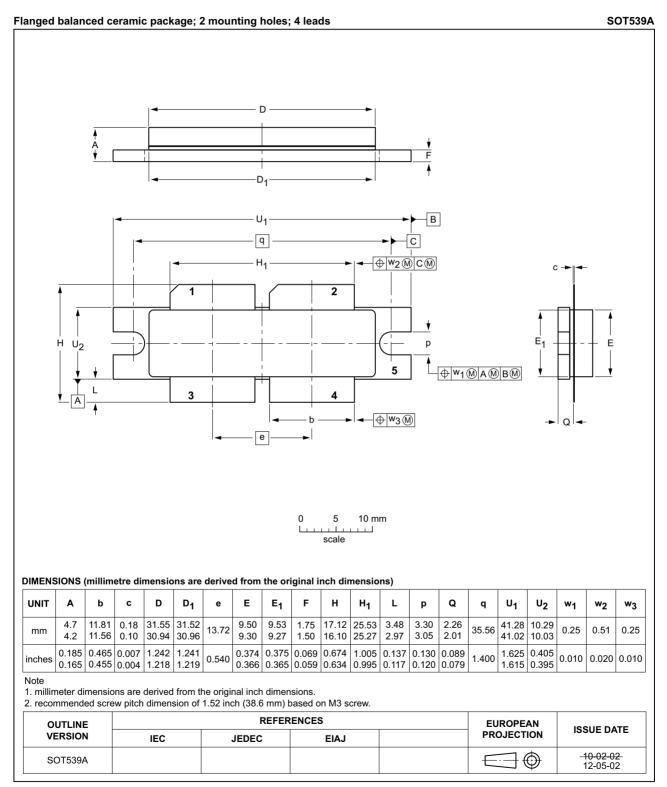
# BLF888E; BLF888ES

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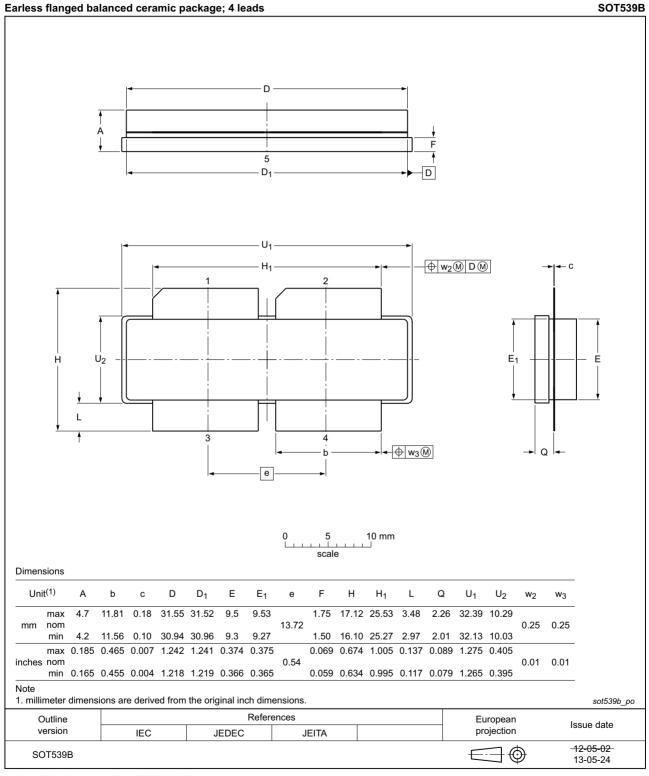
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# 8. Package outline



### Fig 5. Package outline SOT539A

### **UHF power LDMOS transistor**



### Fig 6. Package outline SOT539B

BLF888E\_BLF888ES

# 9. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

# **10. Abbreviations**

Table 10. Abbreviations				
Acronym	Description			
CCDF	Complementary Cumulative Distribution Function			
DVB-T	Digital Video Broadcast - Terrestrial			
ESD	ElectroStatic Discharge			
LDMOS	Laterally Diffused Metal-Oxide Semiconductor			
MTF	Median Time to Failure			
OFDM	Orthogonal Frequency Division Multiplexing			
PAR	Peak-to-Average Ratio			
UHF	Ultra High Frequency			
VSWR	Voltage Standing Wave Ratio			

# 11. Revision history

### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF888E_BLF888ES v.2	20160830	Product data sheet	-	BLF888E_BLF888ES v.1	
Modifications:	<u>Section 1.1 on page 1</u> : section updated				
	• Table 1 on p	age 1: table updated			
	<ul> <li><u>Section 1.2 on page 1</u>: text second list item updated</li> </ul>				
	• Table 5 on p	age <u>3</u> : table updated			
	• Table 6 on p	age 3: table updated			
	• Table 8 on p	age 4: table updated			
	<u>Section 7.1 on page 4</u> : section updated				
	<ul> <li><u>Section 7.3 on page 6</u>: section added</li> </ul>				
BLF888E_BLF888ES v.1	20160317	Objective data sheet	-	-	

# 12. Legal information

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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